# High Directivity

# **Monolithic Amplifier**

# 0.5-2.5 GHz

#### **Product Features**

- 2.8V & 5V operation
- Micro-miniature size .120"X.120"
- Internal DC blocking at RF input and output
- High directivity, 17 dB typ.
- Low noise figure
- Output power, up to +11.4 dBm typ.
- Excellent repeatability
- Low cost
- Aqueous washable

### **Typical Applications**

- Buffer amplifier
- Cellular
- PCN
- Communications satellite
- Defense





MNA-3+

CASE STYLE: DQ849 PRICE: \$1.60 ea. QTY. (30)

+ RoHS compliant in accordance with EU Directive (2002/95/EC)

The +Suffix has been added in order to identify RoHS Compliance. See our web site for RoHS Compliance methodologies and qualifications.

# **General Description**

MNA-3+ is wideband amplifier offering high dynamic range. It has repeatable performance from lot to lot. It is enclosed in a 3x3 mm MCLP plastic package. MNA-3+ is fabricated using GaAs MESFET technology. Expected MTBF at 85°C case temperature is 120,000 years at 2.8V; 60,000 years at 5V.

Function	Pin Number	Description	
RF IN	2	RF input pin	
RF-OUT	5	RF output pin	
DC	7, with 1000 pf	bypass to ground; connect pin 8 via 33 ohms to pin 7 externally	Bias pins
GND	3,4 and paddle in center of bottom		Connections to ground
OPTIONAL	1,6	No internal connection; recommended use: per PCB Layout PL-078	

Mini-Circuits

P.O. Box 350166, Brooklyn, New York 11235-0003 (718) 934-4500 Fax (718) 332-4661 The Design Engineers Search Engine Provides ACTUAL Data Instantly at minicipcuits.com

# **Electrical Specifications at 25°C**

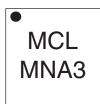
Parameter		Min.	Ту	p.	Max.	Units
Frequency Range		0.5			2.5	GHz
at DC Volts		5.0	5.0	2.8	5.0	V
Gain	f=0.5 GHz		14.6	14.2		dB
	f=1.0 GHz		16.2	15.2		
	f=1.5 GHz		16.1	15.0		
	f=2.0 GHz	13.0	15.0	14.0		
	f=2.5 GHz		11.8	11.0		
Input Return Loss	f=0.75-2.5 GHz		10	10		dB
Output Return Loss	f=0.75-2.5 GHz		14	14		dB
Output Power @ 1 dB compression	f=0.5 GHz		11.4	9.7		dBm
Culput Forest & Fab compression	f=2.5GHz		9.5	8.0		
Output IP3	f=1 GHz		19.6	21.3		dBm
	f=2 GHz		18.0	19.9		
Noise Figure	f=1 GHz		4.9	4.8		dB
Directivity (Isolation - Gain)	Directivity (Isolation - Gain) f=0.5-2.5 GHz		17			
DC Current			30	28	40	mA
Thermal Resistance, junction-to-case		78	8		°C/W	

# **Absolute Maximum Ratings**

Parameter	Ratings		
Operating Temperature	-40°C to 85°C		
Storage Temperature	-55°C to 100°C		
DC Voltage	7V at pin 7 10V at pins 2 & 5		
Power Dissipation	500mW		

Note: Permanent damage may occur if any of these limits are exceeded. These ratings are not intended for continuous normal operation.

## **Product Marking**



#### **Additional Detailed Technical Information**

Additional information is available on our web site. To access this information enter the model number on our web site home page.

Performance data, graphs, s-parameter data set (.zip file)

Case Style: DQ849

MNA-3+: Plastic package, exposed paddle, lead finish: tin/silver/nickel

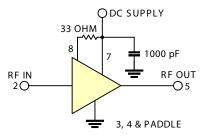
Tape & Reel: F66

Suggested Layout for PCB Design: PL-078

**Evaluation Board: TB-186+** 

**Environmental Ratings: ENV08T1** 

# **Recommended Application Circuit**



For detailed performance specs & shopping online see web site

# **ESD Rating**

Human Body Model (HBM): Class 1A (250v to < 500v) in accordance with ANSI/ESD STM 5.1 - 2001

Charged Device Model (CDM): Class III (500 to 1000v) in accordance with JESD22-C101A

## **MSL** Rating

Moisture Sensitivity: MSL1 in accordance with IPC/JEDEC J-STD-020C

No.	Test Required	Condition	Standard	Quantity
1	Visual Inspection	Low Power Microscope Magnification 40x	MIP-IN-0003 (MCT spec)	45 units
2	Electrical Test	Room Temperature	SCD (MCL spec)	45 units
3	SAM Analysis	Less than 10% growth in term of delamination	J-Std-020C (Jedec Standard)	45 units
4	Moisture Sensitivity Level 1	Bake at 125°C for 24 hours Soak at 85°C/85%RH for 168 hours Reflow 3 cycles at 260°C peak	J-Std-020C (Jedec Standard)	45 units

#### **MSL Test Flow Chart**

